

DYNAMIC CHARACTERISTICS

APT30M36B2LL_LLL

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$		6480		pF
C_{oss}	Output Capacitance			1540		
C_{rss}	Reverse Transfer Capacitance			75		
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 150V$ $I_D = 84A @ 25^\circ C$		115		nC
Q_{gs}	Gate-Source Charge			35		
Q_{gd}	Gate-Drain ("Miller") Charge			45		
$t_{d(on)}$	Turn-on Delay Time	RESISTIVE SWITCHING $V_{GS} = 15V$ $V_{DD} = 150V$ $I_D = 84A @ 25^\circ C$ $R_G = 0.6\Omega$		15		ns
t_r	Rise Time			31		
$t_{d(off)}$	Turn-off Delay Time			29		
t_f	Fall Time			4		
E_{on}	Turn-on Switching Energy ⑥	INDUCTIVE SWITCHING @ 25°C $V_{DD} = 200V, V_{GS} = 15V$ $I_D = 84A, R_G = 5\Omega$		730		μJ
E_{off}	Turn-off Switching Energy			765		
E_{on}	Turn-on Switching Energy ⑥	INDUCTIVE SWITCHING @ 125°C $V_{DD} = 200V, V_{GS} = 15V$ $I_D = 84A, R_G = 5\Omega$		855		
E_{off}	Turn-off Switching Energy			845		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)			84	Amps
I_{SM}	Pulsed Source Current ① (Body Diode)			336	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V, I_S = -84A$)			1.3	Volts
t_{rr}	Reverse Recovery Time ($I_S = -84A, di_S/dt = 100A/\mu s$)		530		ns
Q_{rr}	Reverse Recovery Charge ($I_S = -84A, di_S/dt = 100A/\mu s$)		11.5		μC
dv/dt	Peak Diode Recovery dv/dt ⑤			5	V/ns

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.22	$^\circ C/W$
$R_{\theta JA}$	Junction to Ambient			40	

① Repetitive Rating: Pulse width limited by maximum junction temperature

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting $T_J = +25^\circ C$, $L = 0.71mH$, $R_G = 25\Omega$, Peak $I_L = 84A$

⑤ dv/dt numbers reflect the limitations of the test circuit rather than the device itself. $I_S \leq -I_D 84A$ $di/dt \leq 700A/\mu s$ $V_R \leq 300V$ $T_J \leq 150^\circ C$

⑥ E_{on} includes diode reverse recovery. See figures 18, 20.

APT Reserves the right to change, without notice, the specifications and information contained herein.

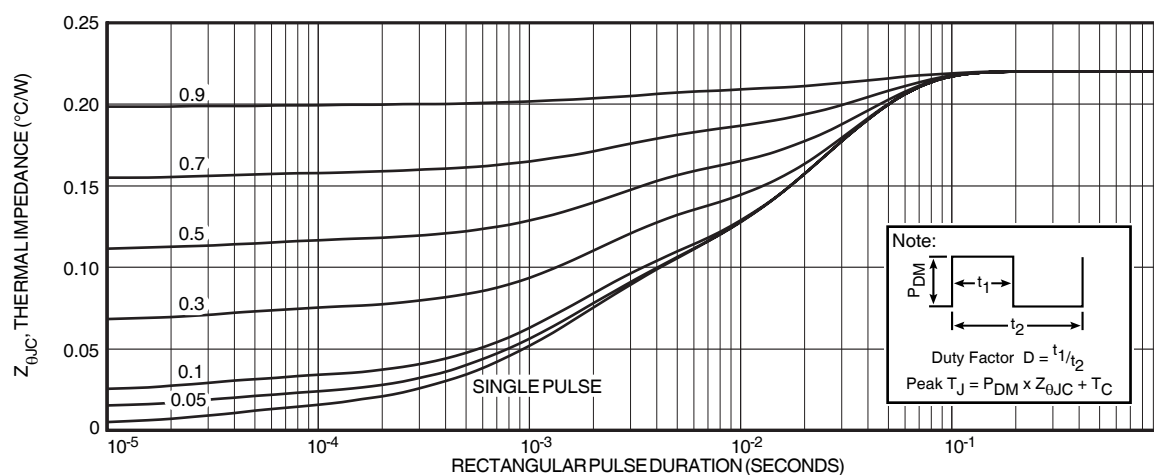


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

Typical Performance Curves

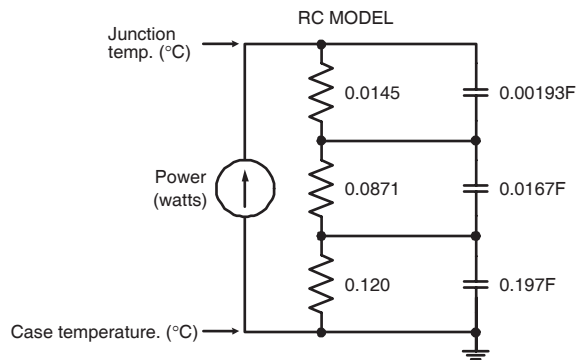


FIGURE 2, TRANSIENT THERMAL IMPEDANCE MODEL

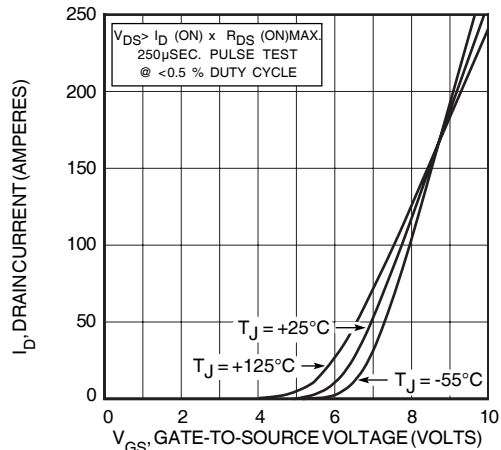


FIGURE 4, TRANSFER CHARACTERISTICS

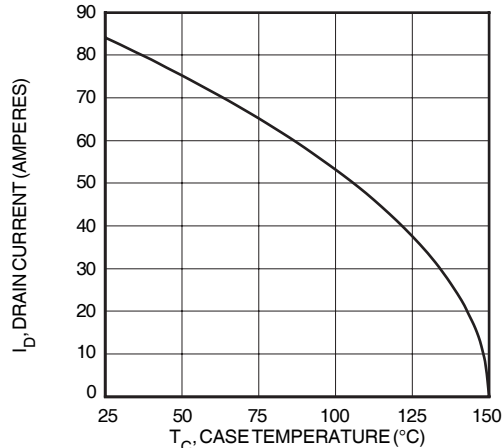


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

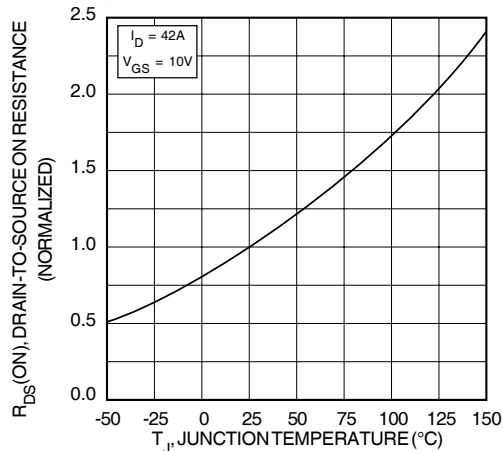


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

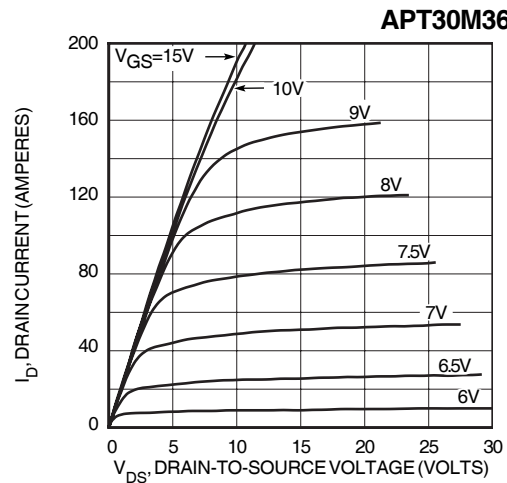


FIGURE 3, LOW VOLTAGE OUTPUT CHARACTERISTICS

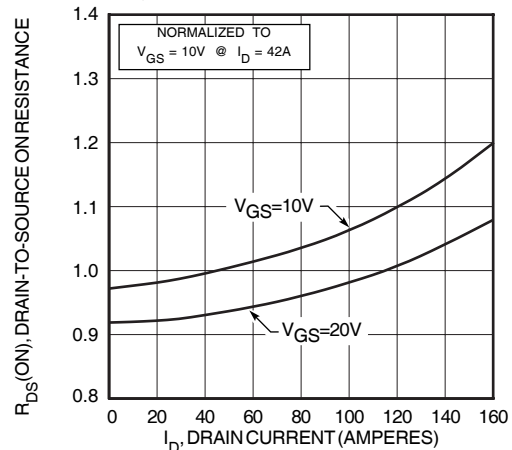


FIGURE 5, $R_{DS}(\text{ON})$ vs DRAIN CURRENT

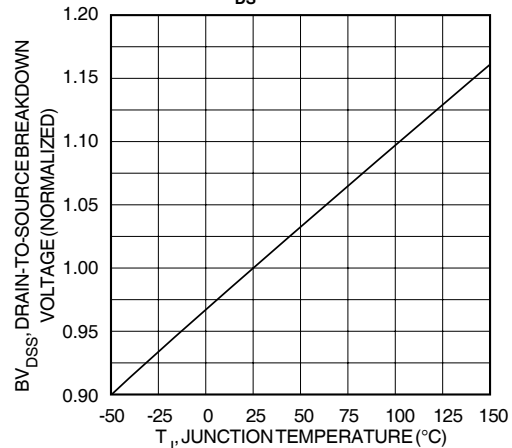


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

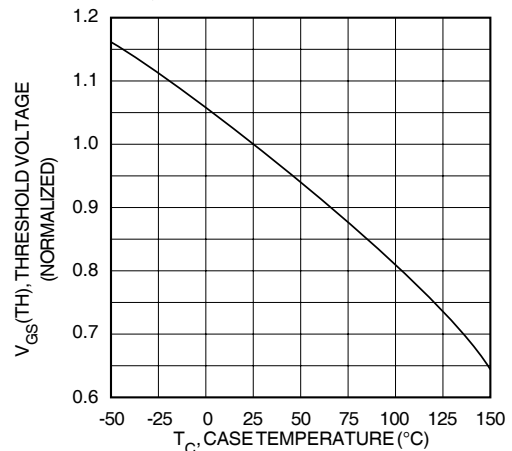


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

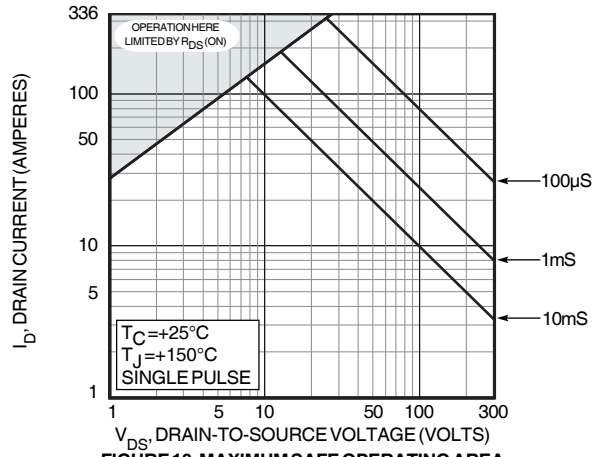


FIGURE 10, MAXIMUM SAFE OPERATING AREA

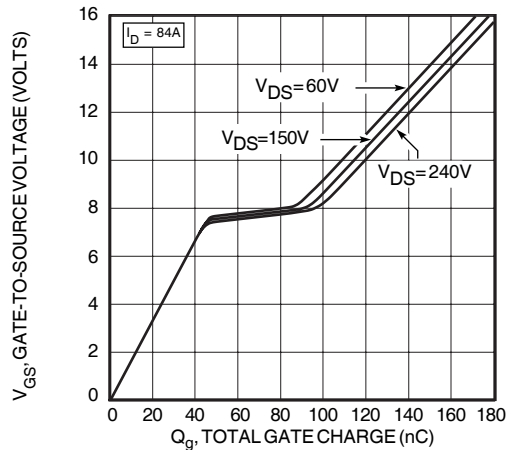


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

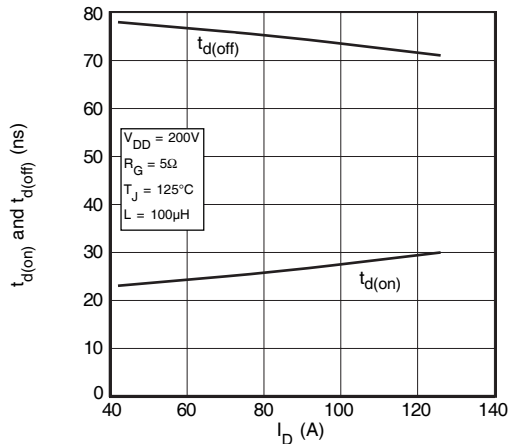


FIGURE 14, DELAY TIMES vs CURRENT

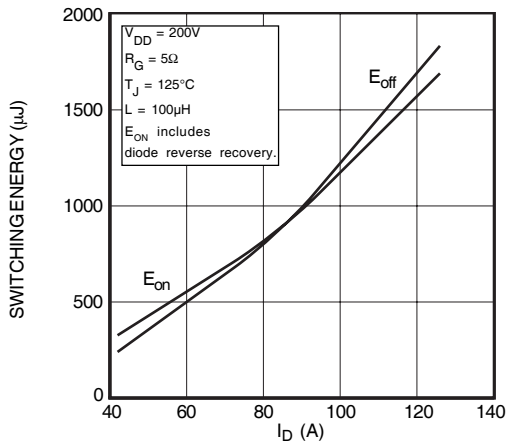


FIGURE 16, SWITCHING ENERGY vs CURRENT

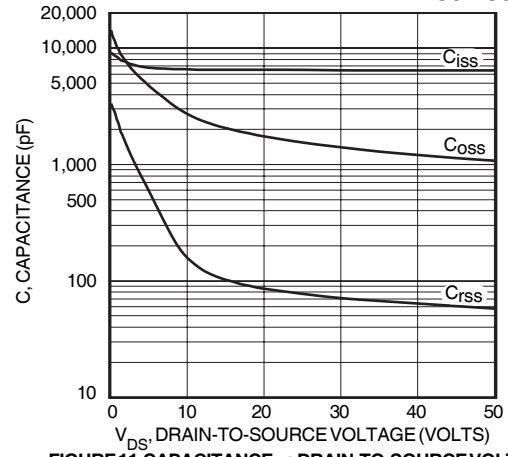


FIGURE 11, CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

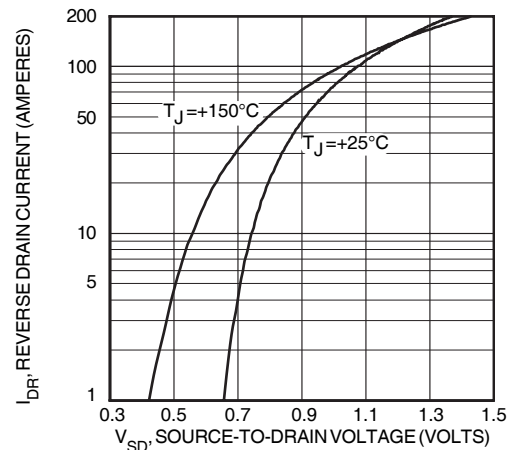


FIGURE 13, SOURCE-DRAIN DIODE FORWARD VOLTAGE

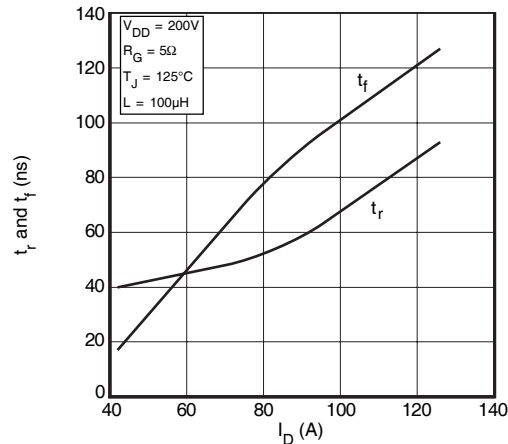


FIGURE 15, RISE AND FALL TIMES vs CURRENT

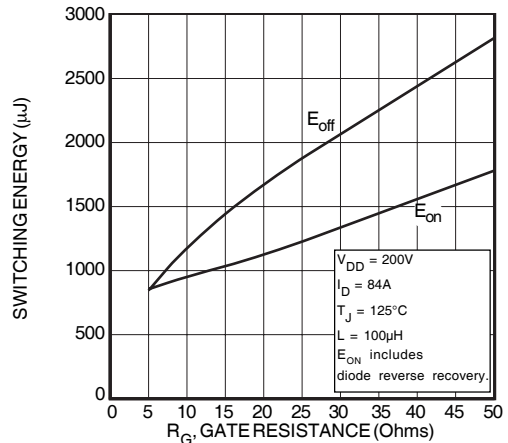


FIGURE 17, SWITCHING ENERGY vs. GATE RESISTANCE

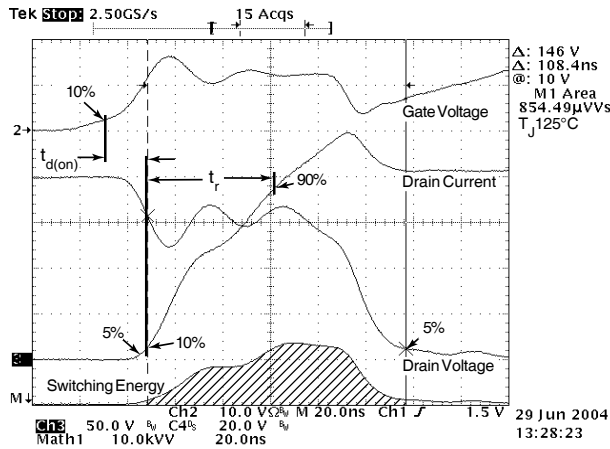


Figure 18, Turn-on Switching Waveforms and Definitions

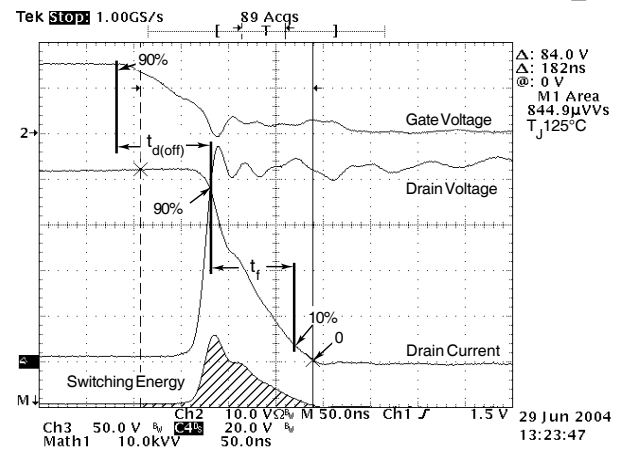


Figure 19, Turn-off Switching Waveforms and Definitions

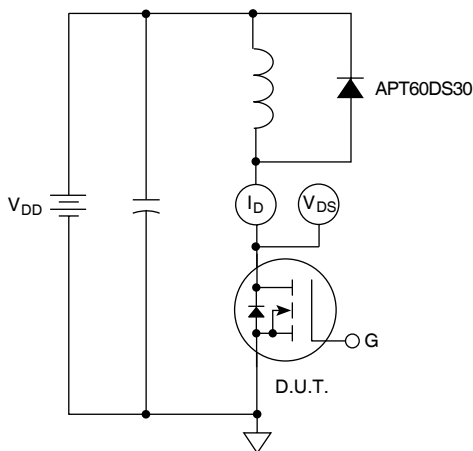
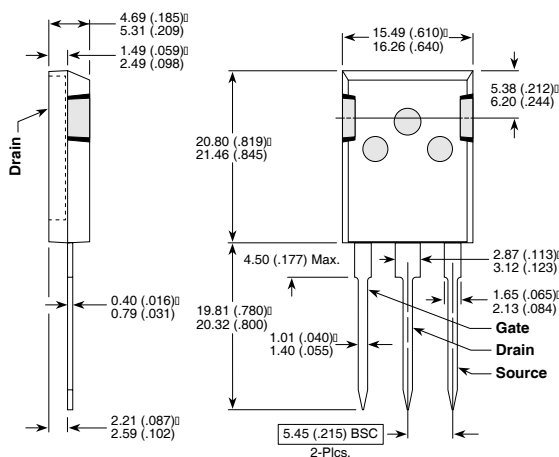


Figure 20, Inductive Switching Test Circuit

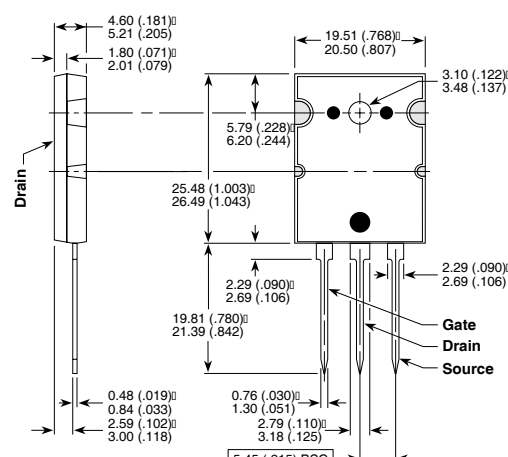
T-MAX™ (B2) Package Outline



These dimensions are equal to the TO-247 without the mounting hole.

Dimensions in Millimeters and (Inches)

TO-264 (L) Package Outline



Dimensions in Millimeters and (Inches)

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522

5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. US and Foreign patents pending. All Rights Reserved.